



67,200-447; TSMC 00-0890
Serial Number 09/975,855

1756
JFLW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

TO: Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

FROM: Tung & Associates
838 West Long Lake Road - Suite 120
Bloomfield Hills, MI 48302

DATE: 8 March 2005

REF: Applicant : Hsieh et al. Filing Date : 11 October 2001
Serial No : 09/975,855 Att'y No. : 67,200-447
Art Unit : 1756 Examiner : Saleha R Mohamedulla
Title : Gap Forming Pattern Fracturing Method for Forming Optical
Proximity Corrected Masking Layer

AMENDMENT AND RESPONSE TO OFFICE ACTION

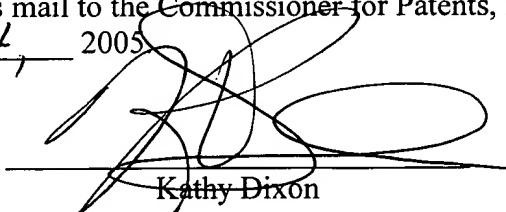
Sir:

In response to an office action mailed 15 December 2004, please consider the following amendments and remarks pertaining to the subject patent application.

There are no amendments to the specification or drawings. Amendments to the claims are contained within a Listing of the Claims that begins on page 2 of this paper. Remarks begin on page 7 of this paper.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being forwarded in an envelope with sufficient postage as first class mail to the Commissioner for Patents, POB 1450, Alexandria, VA 22313-1450 on Mar. 14, 2005.


Kathy Dixon